

## SOT-323 Plastic-Encapsulate Transistors(PNP)

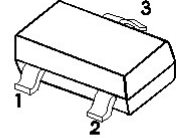
### Features

- Complementary to MMST3904
- Power Dissipation of 200mW
- High Stability and High Reliability
- AEC-Q 101 qualified (Automotive grade with suffix "Q").
- Expsemi electronics.

### Mechanical Data

- SOT-323 Small Outline Plastic Package
- Epoxy UL: 94V-0
- Mounting Position: Any

### SOT-323



1. BASE
2. EMITTER
3. COLLECTOR

Marking: K5N

### Maximum Ratings & Thermal Characteristics

(Ratings at 25°C ambient temperature unless otherwise specified.)

Parameters	Symbol	Value	Unit
Collector-Base Voltage	$V_{CBO}$	-40	V
Collector-Emitter Voltage	$V_{CEO}$	-40	V
Emitter -Base Voltage	$V_{EBO}$	-5	V
Collector Current-Continuous	$I_C$	-200	mA
Collector Power Dissipation	$P_C$	200	mW
Junction Temperature	$T_j$	150	°C
Storage Temperature	$T_{stg}$	-55-+150	°C
Thermal resistance From junction to ambient	$R_{\theta JA}$	625	°C/W

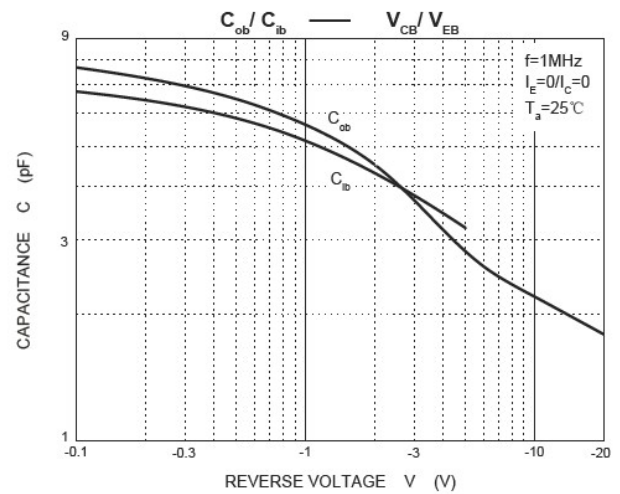
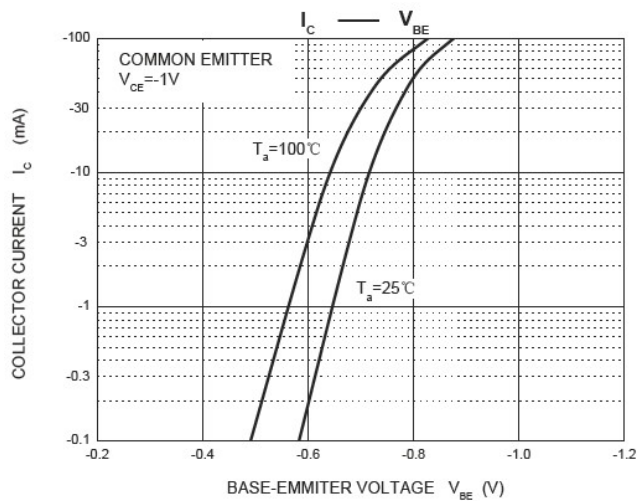
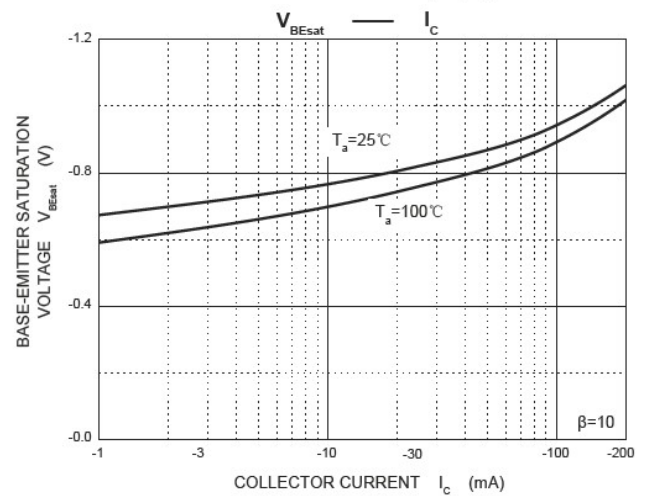
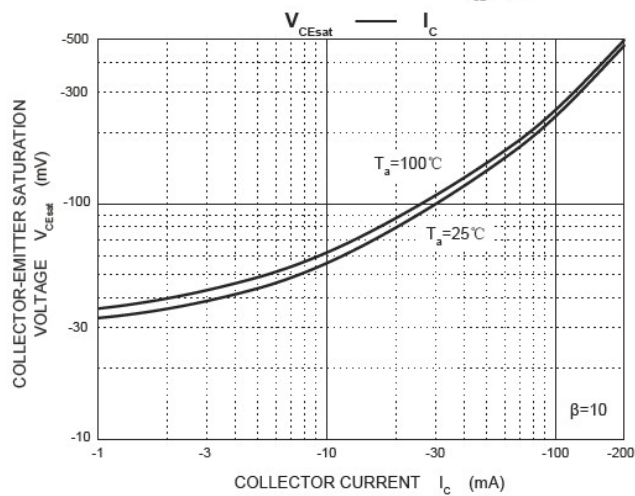
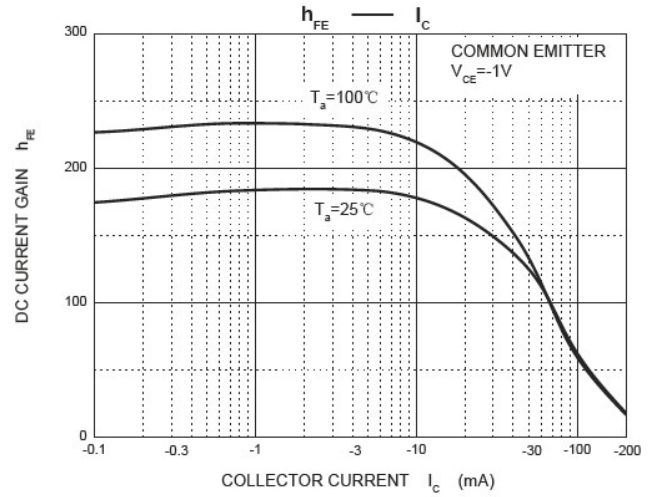
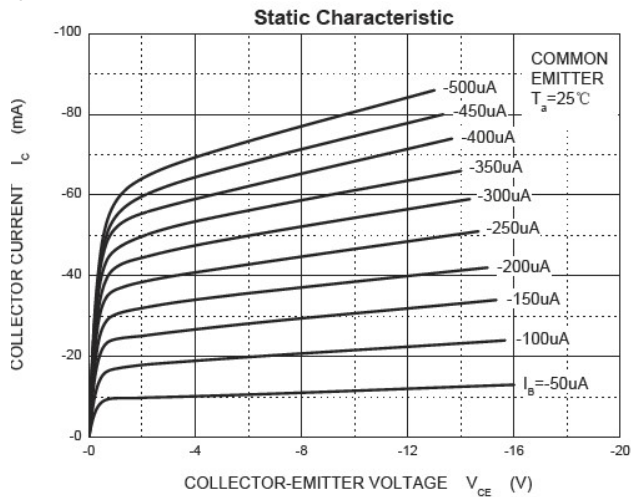
### Electrical Characteristics

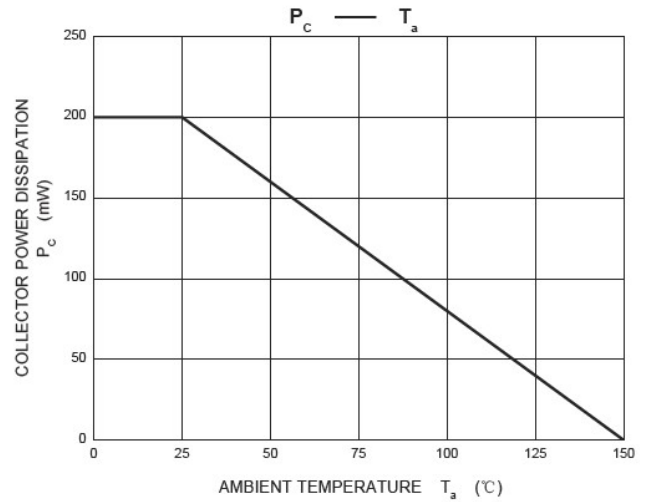
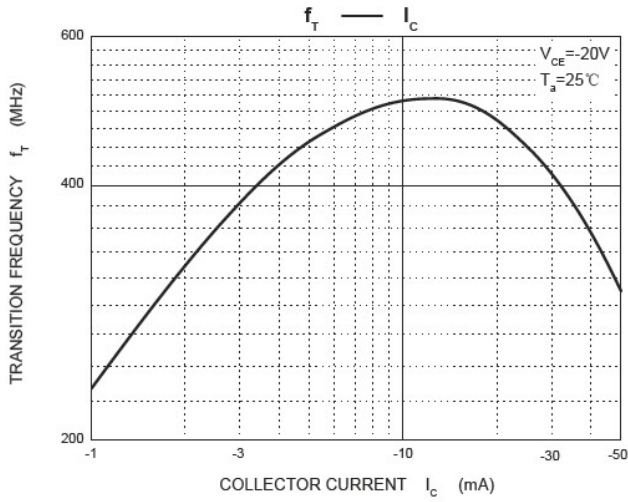
Ratings at 25°C ambient temperature unless otherwise specified

Parameter	Symbols	Test Condition	Limits		Unit
			Min	Max	
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-10\mu A, I_E=0$	-40		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-1mA, I_B=0$	-40		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-10\mu A, I_C=0$	-5		V
Collector cut-off current	$I_{CEX}$	$V_{CE}=-30V, V_{EB(off)}=-3V$		-50	nA
Collector cut-off current	$I_{CBO}$	$V_{CB}=-40V, I_E=0$		-50	nA
DC current gain	$h_{FE(1)}$	$V_{CE}=-1V, I_C=-0.1mA$	60		
	$h_{FE(2)}$	$V_{CE}=-1V, I_C=-1mA$	80		
	$h_{FE(3)}$	$V_{CE}=-1V, I_C=-10mA$	100	300	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-10mA, I_B=-1mA$		-0.20	V
		$I_C=-50mA, I_B=-5mA$		-0.30	V
Base -emitter saturation voltage	$V_{BE(sat)}$	$I_C=-10mA, I_B=-1mA$	-0.65	-0.85	V
		$I_C=-50mA, I_B=-5mA$		-0.95	V
Transition frequency	$f_T$	$V_{CE}=-20V, I_C=-10mA, f=100MHz$	250		MHz
Collector output capacitance	$C_{ob}$	$V_{CB}=-5V, I_E=0, f=1MHz$		4.5	pF
	$C_{ib}$	$V_{EB}=-5V, I_E=0, f=1MHz$		10	pF
Delay time	$t_d$	$V_{CC}=-3V, V_{BE(off)}=-0.5V, I_C=-10mA, I_{B1}=-1mA$		35	nS
Rise time	$t_r$	$V_{CC}=-3V, V_{BE(off)}=-0.5V, I_C=-10mA, I_{B1}=-1mA$		35	nS
Storage time	$t_s$	$V_{CC}=-3V, I_C=-10mA, I_{B1}=I_{B2}=-1mA$		225	nS
Fall time	$t_f$	$V_{CC}=-3V, I_C=-10mA, I_{B1}=I_{B2}=-1mA$		75	nS

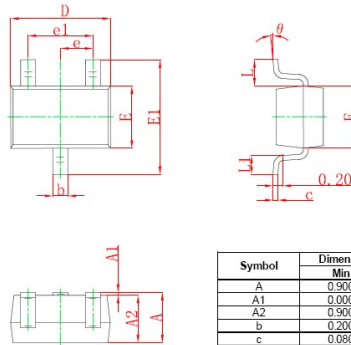
\*Pulse test: pulse width≤300us,duty cycle≤2.0%

Typical characteristics

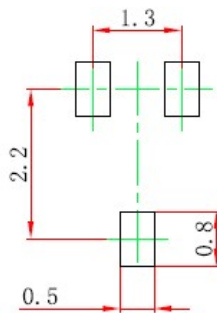




**SOT-323 PACKAGE OUTLINE** Plastic surface mounted package



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.200	0.400	0.008	0.016
c	0.080	0.150	0.003	0.006
D	2.000	2.200	0.079	0.087
E	1.150	1.350	0.045	0.053
E1	2.150	2.450	0.085	0.096
e	0.650 TYP		0.026 TYP	
e1	1.200	1.400	0.047	0.055
L	0.525 REF		0.021 REF	
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°



Note:  
1. Controlling dimension: In millimeters.  
2. General tolerance: ±0.05mm.  
3. The pad layout is for reference purposes only.